

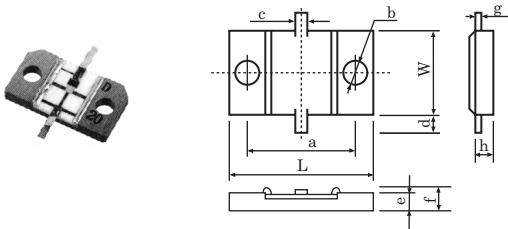


■ Features

- Environmentally friendly, using Aluminium Nitride (N Series)
- Non-cut resistance trimming for high frequency characteristic and stability (Thin film type)
- A variety of custom designs are available

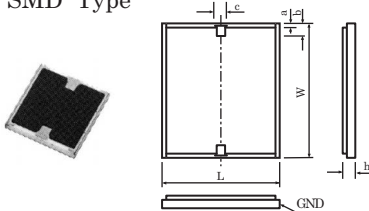
Attenuators

■ Flange Type



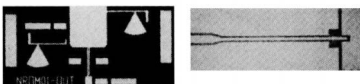
Model No.	Power Rating (W)	Attenuation (dB)	Frequency Characteristics		Dimensions (mm)									
			Freq.(Hz)	VSWR	L	W	a	b	c	d	e	f	g	h
PAT-530	50	30	DC - 4G	1.35	20.6	9.0	14.6	3.5	1.0	3.0	2.6	2.9	0.1	2.4

■ SMD Type



Model No.	Power Rating (W)	Attenuation (dB)	Frequency Characteristics		Dimensions (mm)					
			Freq.(Hz)	VSWR	L	W	a	b	c	h
NSATA-520	50	20	DC - 2G	1.20	8.65	6.7	0.8	1.8	0.9	1.05
			DC - 4G	1.35						
NSATA-530			DC - 3G	1.20						

IC Substrate for MicroWave



Item	Specifications
Substrates	99.5% Al ₂ O ₃ t=0.20, 0.25, 0.38, 0.635mm
Resistive Film	Ta ₂ N designed resistance 25, 50, 100Ω/□
Electrode	NiCr-Au, Au thickness 1~5μm by customer's request
Min.(Line/Space)	30±5μm, The pattern form is custom-made
Features	Bonding is applicable